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PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re U.S. Patent No. 6,897,531 *B2*) Serial No. 10/617,737

Inventor(s): Takashi OHSAWA ) Filed: July 14, 2003

Issue Date: May 24, 2005 ) Attorney Docket No. 002372.00045

For: SEMICONDUCTOR MEMORY DEVICE

**REQUEST FOR CERTIFICATE OF CORRECTION**

U.S. Patent and Trademark Office  
Customer Service Window  
Randolph Building, Mail Stop: Certificate of Correction Branch  
401 Dulany Street  
Alexandria, VA 22314

Certificate  
JAN 19 2006  
of Correction

Sir:

Pursuant to 35 U.S.C. § 254 and 37 C.F.R. § 1.322, this is a request for the issuance of a Certificate of Correction in the above-identified patent. Two (2) copies of PTO Form 1050 are appended. The complete Certificate of Correction involves one page.

The mistakes identified in the appended Form occurred through no fault of the Applicant, as clearly disclosed by the records of the application, which matured into this patent. Enclosed for your convenience is the relevant portion of the Amendment filed November 15, 2004.

Issuance of the Certificate of Correction containing the corrections is respectfully requested. Since these changes are necessitated through no fault of the Applicant, no fee is believed to be associated with this request. Nonetheless, should the Patent and Trademark Office determine that a fee is required, please charge our Deposit Account No. 19-0733.

Respectfully submitted,

BANNER & WITCOFF, LTD.

Dated: January 13, 2006

By: Gary D. Fedorochko  
Gary D. Fedorochko  
Registration No. 35,509

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JAN 20 2006

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO.: 6,897,531 *B2*

DATED: May 24, 2005

INVENTOR(S): Takashi OHSAWA

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In Column 16, Claim 1, Line 63:

Please replace "ton" with --top--

In Column 17, Claim 2, Line 29:

Please replace "sates" with --gates--

Mailing Address of Sender:

Banner & Witcoff, Ltd.  
11th Floor  
1001 G Street, N.W.  
Washington, DC 20001-4597

U.S. PAT. NO 6,897,531

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FORM PTO 1050 (Rev.2-93)

JAN 20 2006

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

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DATED: May 24, 2005

INVENTOR(S): Takashi OHSAWA

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Please replace "ton" with --top--

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U.S. PAT. NO 6,897,531

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FORM PTO 1050 (Rev.2-93)

JAN 20 2006

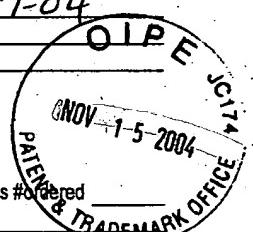
PATENT     DESIGN    B&W Ref. 002372,00045 Date: 11-15-04  
 HAND CARRY Group/Section \_\_\_\_\_ Bldg \_\_\_\_\_ Rm \_\_\_\_\_  
Serial/Patent No.: 101607737 Atty/Sec: GDFLab  
Inventor: OTSUWA Client: KYOWA  
Title: \_\_\_\_\_

The following has been received in the U.S. Patent and Trademark Office on the date stamped hereon:

- |  |  |
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| <input type="checkbox"/> total pp Spec., including : # of Claims   | <input type="checkbox"/> Request for Corrected: <input type="checkbox"/> Filing Receipt <input type="checkbox"/> Assignment    |
| # of independent claims  | <input type="checkbox"/> Abstract  |
| <input type="checkbox"/> Application Data Sheet (ADS): <input type="checkbox"/> Initial <input type="checkbox"/> Supplemental            | <input type="checkbox"/> Response to Restriction/Election Requirement  |
| <input type="checkbox"/> Drawings: <input type="checkbox"/> Formal <input type="checkbox"/> Informal                                     | <input type="checkbox"/> Sequence Listing: <input type="checkbox"/> Diskette <input type="checkbox"/> Paper    pages _____     |
| # of distinct sheets _____   | <input type="checkbox"/> Amendment <input type="checkbox"/> Response : OA <u>9-7-04</u>  |
| Figs: _____  | <input type="checkbox"/> Petition for Extension of Time until _____  |
| <input type="checkbox"/> Nonpublication Request  | <input type="checkbox"/> RCE <input type="checkbox"/> w/Ext of Time : OA dtd _____   |
| <input type="checkbox"/> Declaration/Power of Attorney: <input checked="" type="checkbox"/> Executed <input type="checkbox"/> Unexecuted | <input type="checkbox"/> Request for Approval of Drawing Changes   |
| <input type="checkbox"/> Assignment w/PTO Cover Sheet  | <input type="checkbox"/> Notice of Appeal & Fee  |
| <input type="checkbox"/> IDS w/PTO 1449 <input type="checkbox"/> References <input type="checkbox"/> w/Fee                               | <input type="checkbox"/> Brief <input type="checkbox"/> Appeal & Fee <input type="checkbox"/> Reply                            |
| <input type="checkbox"/> Preliminary Amendment   | <input type="checkbox"/> Request for Oral Hearing  |
| <input type="checkbox"/> Priority Claim: (Foreign or U.S. Provisional) B&W# _____  | <input type="checkbox"/> Issue Fee <input type="checkbox"/> Pub. Fee <input type="checkbox"/> Adv. Pat. Copies # ordered _____ |

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|---|--|---|---|
| Country   | Appl. #  | Date  |   |
| <input type="checkbox"/> w/Foreign Priority Document(s)                                   |  |   |   |
| <input type="checkbox"/> Application:   | <input type="checkbox"/> CIP <input type="checkbox"/> Continuation <input type="checkbox"/> Divisional | <input type="checkbox"/> Amendment under 37 CFR 1.312   |   |
| Parent SN:  | B&W#   | <input type="checkbox"/> Request for Certificate of Correction  |   |
| <input type="checkbox"/> U.S. Provisional   | pp Spec/Claims; Cover Sheet  | <input type="checkbox"/> Transmittal <input type="checkbox"/> Fee Transmittal w/Auth. to Charge Deposit Acct. |   |
| <input type="checkbox"/> Response to Missing Parts/Requirements dtd <u>10</u>             |  |   | <input type="checkbox"/> Certificate of Mailing       |
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B&W Rev. 01/04



Appn. No.: 10/617,737  
Amendment dated November 15, 2004  
Reply to Office Action of September 7, 2004

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

|                                  |                                |
|----------------------------------|--------------------------------|
| In re the Application of:        | Atty. Docket No.: 002372.00045 |
| <b>Takashi OHSAWA</b>            |                                |
| Serial No.: 10/617,737           | Group Art Unit: 2815           |
| Filed: July 14, 2003             | Examiner: Wilson, A.           |
| For: SEMICONDUCTOR MEMORY DEVICE | Confirmation No.: 3632         |

**AMENDMENT**

U.S. Patent and Trademark Office  
220 20th Street S.  
Customer Window, Mail Stop Amendment  
Crystal Plaza Two, Lobby, Room 1B03  
Arlington, VA 22202

Sir:

In response to the Office Action mailed September 7, 2004, please amend the instant application as follows:

**Amendments to the Claims** are reflected in the Listing of Claims, which begins on page 2 of this paper.

**Remarks/Arguments** begin on page 6 of this paper.

An **Appendix** including amended drawing figures is attached following page 7 of this paper.

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claims 1-5 (canceled)

Claim 6 (currently amended): A The semiconductor memory device according to claim 4, having full depletion type MISFETs to constitute memory cells on a semiconductor substrate via an insulating film, each of the MISFETs comprising:

a semiconductor layer formed on the insulating film;

a source region formed in the semiconductor layer;

a drain region formed apart from the source region in the semiconductor layer, the semiconductor layer between the source region and the drain region serving as a channel body in a floating state;

a main gate formed on a first side of the channel body to form a channel in the channel body; and

an auxiliary gate formed on a second side of the channel body, the second side being opposite to the first side, a portion of the second side of the channel body being capable of accumulating majority carriers under conditions in which the channel body is fully depleted by an electric field from the main gate and an electric field is applied to the channel body from the auxiliary gate,

wherein the MISFET has a first data state in which the majority carriers are accumulated in the portion of the second side of the channel body and a second data state in which the majority carriers accumulated in the portion of the second side of the channel body are emitted,

wherein the MISFETs are arranged in the form of a matrix to constitute a cell array, the drain regions are connected to bit lines, the main gates constitute word lines intersecting the bit lines, the source regions are connected to a fixed potential line and the auxiliary gate is formed as a common electrode shared among the memory cells,

wherein the first side of the channel body is a top side face of the semiconductor layer, the second side of the channel body is a back side face of the semiconductor layer and the main gate is formed on the top side face via a gate insulating film, and

wherein the auxiliary gate is an impurity doping layer buried between the semiconductor substrate and the insulating film.

Claim 7 (canceled)

Claim 8 (currently amended): A The semiconductor memory device according to claim 1, having full depletion type MISFETs to constitute memory cells on a semiconductor substrate via an insulating film, each of the MISFETs comprising:

a semiconductor layer formed on the insulating film;

a source region formed in the semiconductor layer;

a drain region formed apart from the source region in the semiconductor layer, the semiconductor layer between the source region and the drain region serving as a channel body in a floating state;

a main gate formed on a first side of the channel body to form a channel in the channel body; and

an auxiliary gate formed on a second side of the channel body, the second side being opposite to the first side, a portion of the second side of the channel body being capable of accumulating majority carriers under conditions in which the channel body is fully depleted by an electric field from the main gate and an electric field is applied to the channel body from the auxiliary gate,

wherein the MISFET has a first data state in which the majority carriers are accumulated in the portion of the second side of the channel body and a second data state in which the majority carriers accumulated in the portion of the second side of the channel body are emitted,

wherein the MISFETs are arranged in the form of a matrix to constitute a cell array, the drain regions are connected to bit lines, the main gates constitute word lines intersecting the bit lines, the source regions are connected to a fixed potential line and the auxiliary gate is formed as a common electrode shared among the memory cells, and